

ABSTRACT OF THE DISCLOSURE

A method is provided for turning off MOS transistors through an anti-code (type) LDD implant without the need for high energy implant that causes poly damage. The method also negates any deleterious effects due to the variations in the thickness of the poly gate. The anti-code LDD implant can be performed vertically, or at a tilt angle, or in a combination of vertical and tilt angle. The method can be made part of a Flash-ROM process that is applicable to both polycide and silicide processes.